

ABSTRACT OF THE INVENTION

The present invention is a novel cleaning method and a solution for use in a single wafer cleaning process. According to the present invention the cleaning solution comprises ammonium hydroxide (NH_4OH), hydrogen peroxide (H_2O_2), water (H_2O) and a chelating agent. In an embodiment of the present invention the cleaning solution also contains a surfactant. And still yet another embodiment of the present invention the cleaning solution also comprises a dissolved gas such as H_2 . In a particular embodiment of the present invention, this solution is used by spraying or dispensing it on a spinning wafer.

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